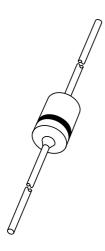
DISCRETE SEMICONDUCTORS

DATA SHEET



BA221High-speed diode

Product specification Supersedes data of April 1996 1996 Sep 03





High-speed diode

BA221

FEATURES

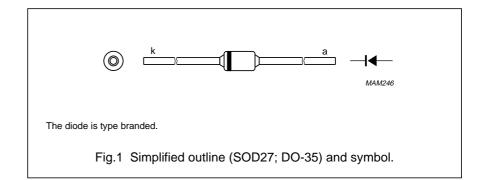
- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- · General application
- Continuous reverse voltage: max. 30 V
- Repetitive peak reverse voltage: max. 30 V
- Repetitive peak forward current: max. 400 mA.

APPLICATIONS

· High-speed switching.

DESCRIPTION

The BA221 is a high-speed switching diode fabricated in planar technology, and encapsulated in the hermetically sealed leaded glass SOD27 (DO-35) package.



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage		_	30	V
V_R	continuous reverse voltage		_	30	V
I _F	continuous forward current	see Fig.2; note 1	_	200	mA
I _{FRM}	repetitive peak forward current		_	400	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	9	A
		t = 100 μs	_	3	Α
		t = 1 s	_	1	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	350	mW
T _{stg}	storage temperature		-65	+200	°C
Tj	junction temperature		_	200	°C

Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

High-speed diode

BA221

ELECTRICAL CHARACTERISTICS

 T_j = 25 °C; unless otherwise specified.

PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
forward voltage	see Fig.3			
	I _F = 1 mA	_	625	mV
	I _F = 100 mA	_	950	mV
	I _F = 200 mA	_	1050	mV
reverse current	see Fig.5			
	V _R = 10 V	_	25	nA
	V _R = 30 V	_	200	nA
	V _R = 10 V; T _j = 150 °C	_	50	μΑ
	V _R = 30 V; T _j = 150 °C	_	100	μΑ
diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	_	2.5	pF
reverse recovery time	when switched from I _F = 10 mA to	_	4	ns
	1 11			
	measured at I _R = 1 mA; see Fig.7			
forward recovery voltage	when switched from $I_F = 400$ mA; $t_r = 30$ ns; see Fig.8	_	2.0	V
	forward voltage reverse current diode capacitance reverse recovery time	$\label{eq:see-fig.3} \begin{cases} I_F = 1 \text{ mA} \\ I_F = 100 \text{ mA} \\ I_F = 200 \text{ mA} \end{cases}$ reverse current $\begin{aligned} \text{see Fig.5} \\ V_R = 10 \text{ V} \\ V_R = 30 \text{ V} \\ V_R = 10 \text{ V}; T_j = 150 \text{ °C} \\ V_R = 30 \text{ V}; T_j = 150 \text{ °C} \end{aligned}$ diode capacitance $\begin{aligned} f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.6} \\ \text{reverse recovery time} \end{aligned}$ when switched from $I_F = 10 \text{ mA to} \\ I_R = 60 \text{ mA}; R_L = 100 \ \Omega; \\ \text{measured at } I_R = 1 \text{ mA}; \text{ see Fig.7} \end{aligned}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
R _{th j-a}	thermal resistance from junction to ambient	lead length 10 mm; note 1	500	K/W

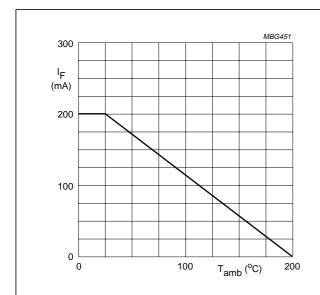
Note

1. Device mounted on a printed circuit-board without metallization pad.

High-speed diode

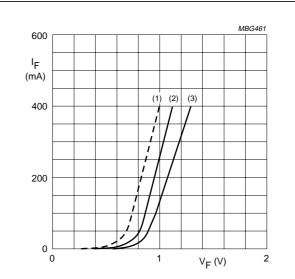
BA221

GRAPHICAL DATA



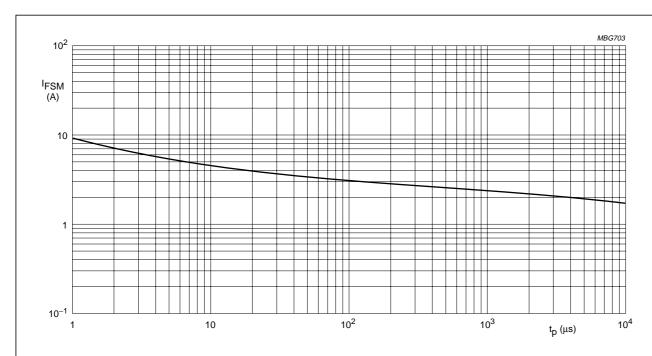
Device mounted on an FR4 printed-circuit board; lead length 10 mm.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 175$ °C; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



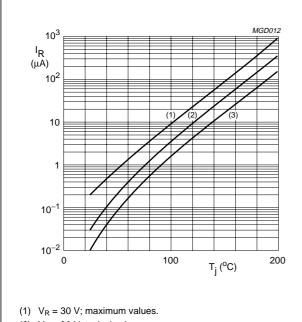
Based on square wave currents.

 T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

High-speed diode

BA221



- (2) $V_R = 30 \text{ V}$; typical values.
- (3) $V_R = 10 \text{ V}$; typical values.

Fig.5 Reverse current as a function of junction temperature.

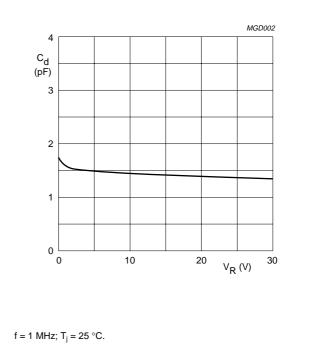
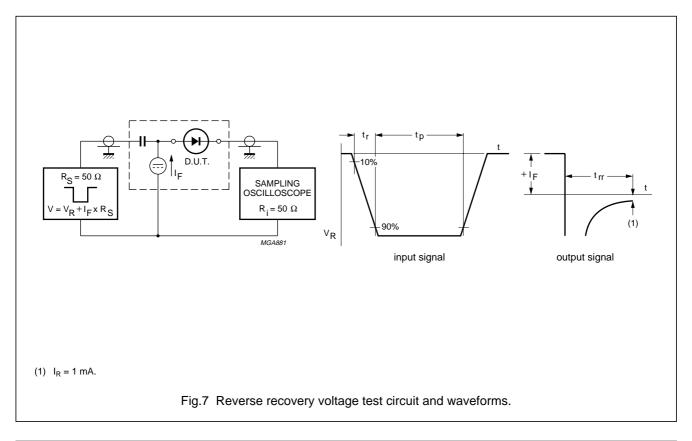
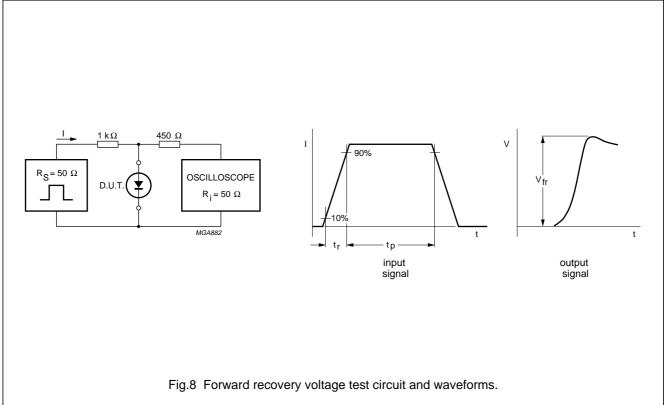


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diode

BA221





6

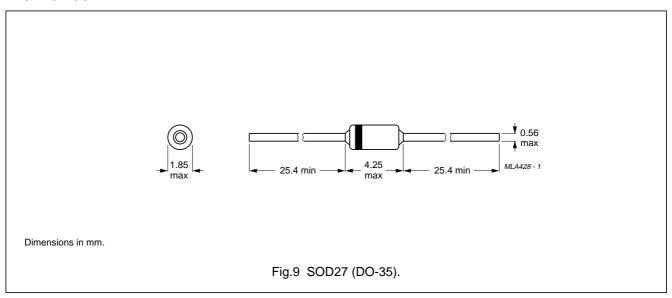
1996 Sep 03

Product specification Philips Semiconductors

High-speed diode

BA221

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		

Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

7 1996 Sep 03